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Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method ~~for manufacturing to manufacture~~ a semiconductor device, ~~characterized in comprising:~~
 - ~~a step of~~ forming opening sections in a semiconductor substrate;
 - ~~a step of~~ forming embedded electrodes inside the opening sections; and
 - ~~a step of~~ spin etching the semiconductor substrate from a back surface of a surface of the semiconductor substrate where the opening sections are formed, to thereby thin down the semiconductor substrate and make the opening sections penetrate the semiconductor substrate.
2. (Currently Amended) A ~~The~~ method ~~for manufacturing to manufacture~~ a semiconductor device according to claim 1, ~~characterized in further comprising:~~
 - ~~a step of~~ forming dielectric films inside the opening sections before ~~the step of~~ forming the embedded electrodes inside the opening sections; and
 - ~~a step of~~ exposing at least one part of the dielectric films in ~~the step of~~ making the opening sections penetrate the semiconductor substrate.
3. (Currently Amended) A ~~The~~ method ~~for manufacturing to manufacture~~ a semiconductor device according to claim 2, ~~characterized in further comprising comprising:~~
 - ~~a step of~~ removing the dielectric films before ~~the step of~~ making the opening sections penetrate the semiconductor substrate to expose the embedded electrodes.
4. (Currently Amended) A ~~The~~ method ~~for manufacturing to manufacture~~ a semiconductor device according to claim 1, ~~characterized in further comprising comprising:~~
 - ~~a step of~~ grinding the semiconductor substrate from the back surface thereof before ~~the step of~~ making the opening sections penetrate the semiconductor substrate.

5. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor device according to claim 1, ~~characterized in that, in the step of making the~~ opening sections penetrate the semiconductor substrate, an etching rate for the semiconductor substrate ~~changes~~ changing with time.

6. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor device according to claim 1, ~~characterized in that, in the step of making the~~ opening sections penetrate the semiconductor substrate, the etching rate for the semiconductor substrate ~~changes~~ changing from a first etching rate to a second etching rate that is lower than the first etching rate.

7. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor device according to claim 3, ~~characterized in that, in the step of exposing the~~ embedded electrodes, the dielectric films are removed by grinding the dielectric films exposed.

8. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor device according to claim 1, ~~characterized in further comprising comprising:~~ _____ ~~a step of attaching a retaining member on the surface of the semiconductor~~ substrate where the opening sections are formed, before ~~the step of making the opening~~ sections penetrate the semiconductor substrate.

9. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor device according to claim 8, ~~characterized in that the retaining member~~ ~~includes~~ including a base member and an adhesive layer provided on a surface of the base member, and the base member ~~is~~ being one of a tape, a film, a light-transmissive substrate and another substrate.

10. (Currently Amended) ~~A~~ The method for manufacturing to manufacture a semiconductor module, ~~characterized in comprising:~~

~~a step of~~ forming opening sections in a first semiconductor substrate;

~~a step of~~ forming embedded electrodes inside the opening sections;

~~a step of~~ spin etching the semiconductor substrate from a back surface of a

surface of the semiconductor substrate where the opening sections are formed, to thereby thin down the semiconductor substrate and make the opening sections penetrate the semiconductor substrate; and

~~a step of~~ mounting the first semiconductor substrate on a second

semiconductor substrate having electrodes, and electrically connecting the embedded electrodes and the electrodes.